MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK8P60W5

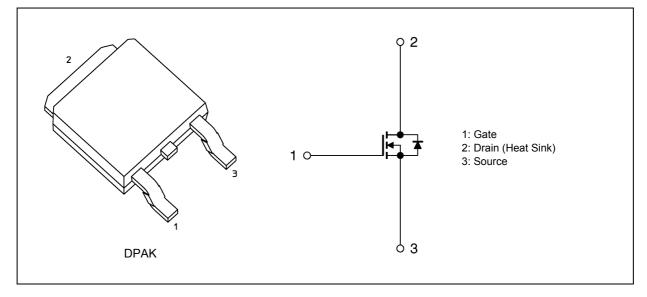
1. Applications

- Switching Voltage Regulators
- Motor Drivers

2. Features

- (1) Fast reverse recovery time: $t_{rr} = 80$ ns (typ.)
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 0.44 \Omega$ (typ.) by used to Super Junction Structure : DTMOS
- (3) Easy to control Gate switching
- (4) Enhancement mode: V_{th} = 3 to 4.5 V (V_{DS} = 10 V, I_{D} = 0.4 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	600	V
Gate-source voltage		V _{GSS}	±30	
Drain current (DC)	(Note 1)	Ι _D	8.0	Α
Drain current (pulsed)	(Note 1)	I _{DP}	32	
Power dissipation (T _c = 2	:5°C)	PD	80	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	105	mJ
Avalanche current		I _{AR}	2.0	Α
Reverse drain current (DC)	(Note 1)	I _{DR}	8.0	
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	32	
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Мах	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	1.57	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_DD = 90 V, T_ch = 25°C (initial), L = 46.0 mH, R_G = 25 Ω , I_AR = 2.0 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	—	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	600	—	_	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.4 mA	3	_	4.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 4.0 A		0.44	0.56	Ω

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 1 MHz		590	_	pF
Reverse transfer capacitance	C _{rss}]		1.7	_	
Output capacitance	C _{oss}]		16	_	
Effective output capacitance	C _{o(er)}	$V_{DS} = 0$ to 400 V, $V_{GS} = 0$ V		33		
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz		7.5	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1		40	_	ns
Switching time (turn-on time)	t _{on}	1		60	_	
Switching time (fall time)	t _f			5.5	_	
Switching time (turn-off time)	t _{off}	1		70		
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 4.0 A	50	_	_	V/ns

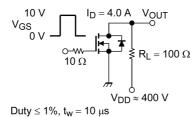


Fig. 6.2.1 Switching Time Test Circuit

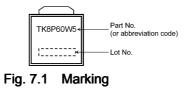
6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, \text{I}_{D} = 8.0 \text{ A}$	—	22	—	nC
Gate-source charge 1	Q _{gs1}		_	7.5	_	
Gate-drain charge	Q _{gd}		_	13	_	

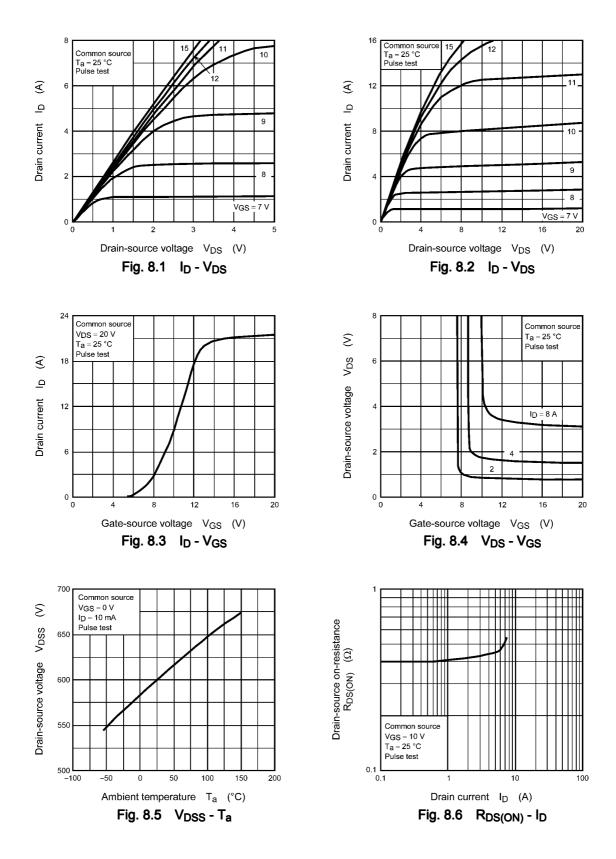
6.4. Source-Drain Characteristics (Ta = 25°C unless otherwise specified)

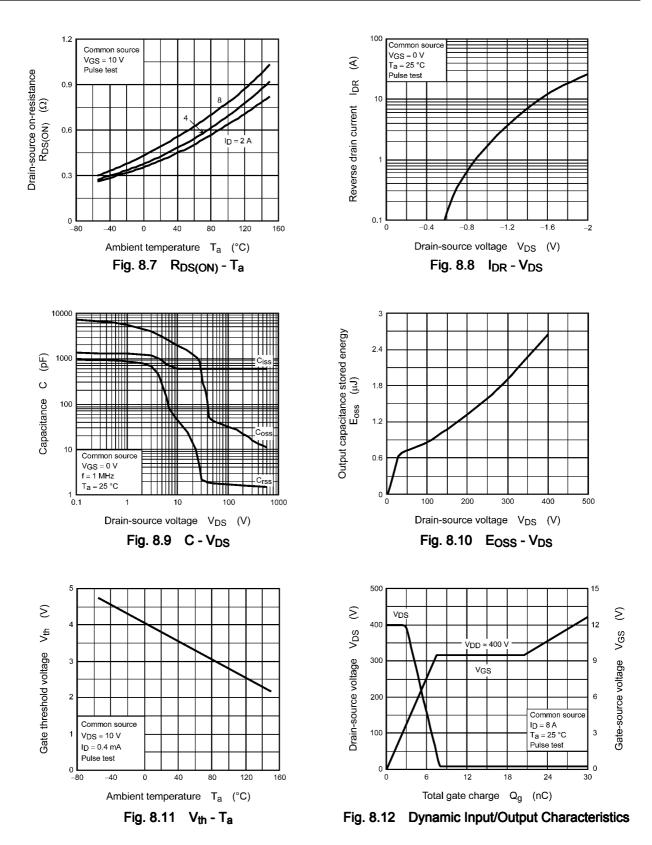
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 8.0 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 4.0 A, V _{GS} = 0 V		80	128	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 100 A/μs	_	0.35	_	μC
Peak reverse recovery current	Irr			9.2	_	А
Diode dv/dt ruggedness	dv/dt	I _{DR} = 4.0 A, V _{GS} = 0 V, V _{DD} = 400 V	50			V/ns

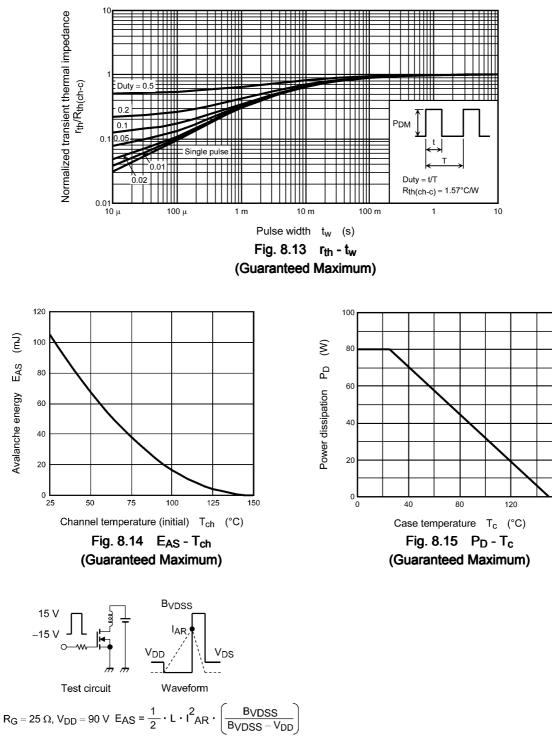
7. Marking

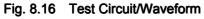


8. Characteristics Curves (Note)

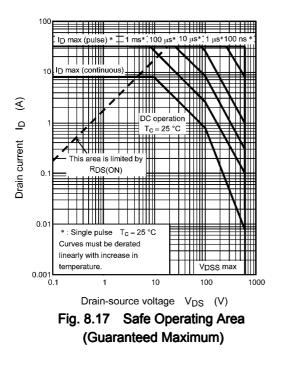








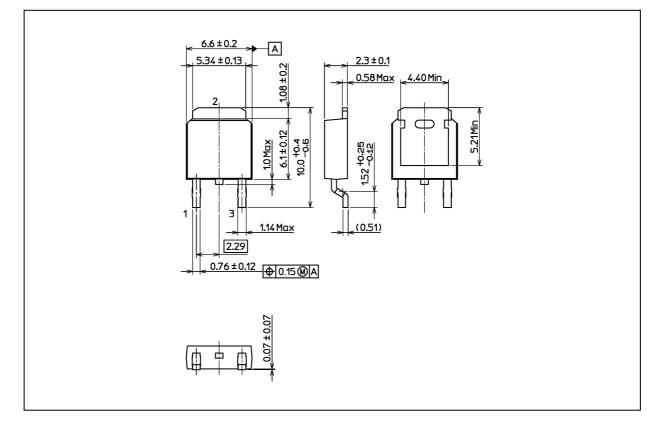
160



Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

	Package Name(s)
TOSHIBA: 2-7K1S	
Nickname: DPAK	

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